	L #	Hits	Search Text	DBs
1	L1	170545	"438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	148	1 and (FinFET or ((fin-type or dual-gate? or double-gate?) near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	0	2 and H-shaped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	0	2 and align$5 near mark?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	0	2 and gate and spacer and (additional near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L6	2	2 and (extrinsic near resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	179	(anderson-brent-a or nowak-edward-j).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	50	7 and (FinFET or ((fin-type or dual-gate? or double-gate?) near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L9	0	8 and (align$5 or mark?) and (additional near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L10	97	(FinFET or ((fin-type or dual-gate? or double-gate?) near transistor)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L11	0	10 and (H-shaped or (h near shaped))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L12	0	(FinFET or ((fin-type or dual-gate? or double-gate?) near transistor)) and gate and spacer and H-shap$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L14	0	13 and (grow$3 near additional near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	L15	0	13 and (low$3 near extrinsic near resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	L #	Hits	Search Text	DBs
15	L13	169	(FinFET or ((fin-type or dual-gate? or double-gate?) near transistor)) and gate and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB